

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4091	electrostatic and semiconductor and pad	US-PGPUB	OR	ON	2006/02/13 08:29
L2	1197	(electrostatic near discharge) and semiconductor and pad	US-PGPUB	OR	ON	2006/02/13 08:29
S1	1	10/720846	US-PGPUB	OR	ON	2006/02/13 08:28
S2	148110	("257").CLAS.	USPAT; USOCR	OR	OFF	2006/02/11 13:42
S3	9410	S2 and (single near crystal near (Si or silicon))	US-PGPUB; USPAT	OR	ON	2006/02/11 13:42
S4	7422	S3 and well	US-PGPUB; USPAT	OR	ON	2006/02/11 13:43
S5	1620	S4 and (well same connect\$3)	US-PGPUB; USPAT	OR	ON	2006/02/11 13:50
S6	847	S4 and (well same connect\$3) and insulat\$3 and p-type and n-type	US-PGPUB; USPAT	OR	ON	2006/02/11 14:48
S7	232	S4 and (well same connect\$3) and insulat\$3 and p-type and n-type and soi	US-PGPUB; USPAT	OR	ON	2006/02/12 14:17
S8	148974	("257").CLAS.	USPAT; USOCR	OR	OFF	2006/02/12 11:16
S9	9475	S8 and (single near crystal near (Si or silicon))	US-PGPUB; USPAT	OR	ON	2006/02/12 11:16
S10	7470	S9 and well	US-PGPUB; USPAT	OR	ON	2006/02/12 11:16
S11	233	S10 and (well same connect\$3) and insulat\$3 and p-type and n-type and soi and ("single crystal " with (silicon or Si))	US-PGPUB; USPAT	OR	ON	2006/02/12 11:18
S13	1	ratten.in.	US-PGPUB; USPAT	OR	ON	2006/02/12 14:18
S14	213	voldman.in.	US-PGPUB; USPAT	OR	ON	2006/02/12 14:19
S15	0	voldman,steven.in.	US-PGPUB; USPAT	OR	ON	2006/02/12 14:19
S16	0	voldman-steven.in.	US-PGPUB; USPAT	OR	ON	2006/02/12 14:19
S17	206	voldman and steven.in.	US-PGPUB; USPAT	OR	ON	2006/02/12 14:42

S18	28	("3791024" "4104086" "4256514" "4283249" "4473598" "4505893" "4889829" "4907053" "4989057" "5258318" "5308782" "5312777" "5371401" "5376562" "5399507" "5470776" "5521401" "5604137" "5606186" "5612552").PN. OR ("6071803").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/12 14:25
S19	1	("4104086").PN.	USPAT	OR	OFF	2006/02/12 17:08
S20	2932	semiconductor and (electrostatic same pad)	US-PGPUB; USPAT	OR	ON	2006/02/12 17:09